TT Type High Precision TCXO

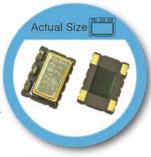
7.0 x 5.0 mm SMD Voltage Controlled Temperature **Compensated Crystal Oscillator**

FEATURE

- Typical 7.0 x 5.0 x 1.9 mm ceramic SMD package.
- High Precision for -40°C $\sim +85$ °C, ± 0.28 ppm , -40°C $\sim +105$ °C , ± 2 ppm.
- CMOS and Clipped Sine wave (without DC-cut capacitor) output optional.

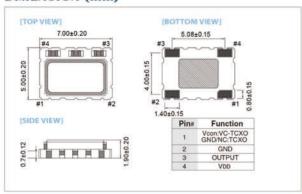
TYPICAL APPLICATION

- Femtocell , Base Stations
- WLAN/WiMAX/WIFI, Wireless Communications

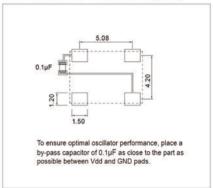


RoHS Compliant

DIMENSION (mm)



SOLDER PAD LAYOUT (mm)



ELECTRICAL SPECIFICATION

Parameter	5.0 V		3.3V		Unit	
	Min. Max.		Min. Max.			
Supply Voltage Variation (VDD)	VDD-5%	VDD+5%	VDD-5%	VDD+5%	V	
Frequency Range	5	52	5	52	MHz	
Standard Frequency	10, 12.8, 16.384, 19.2, 19.44, 20, 25, 26					
Frequency Tolerance*	(30)	±2.0	56	±2.0	ppm	
Frequency Stability						
Vs Supply Voltage (±5%) change	-	±0.1	-	±0.05	ppm	
Vs Load (±10%) change	<u> </u>	±0.05	_	±0.05		
Vs Aging (@1st year)	177	±1.0		±1.0	ppm / yea	
Supply Current (CMOS output)	-	6	-	6		
Supply Current (Clipped Sine Wave)	120	3.5	2	3.5	mA	
Output Level (CMOS) Output High (Logic "1")	90%VDD	-	90%Vpp	-	V	
Output Low (Logic "0")	(#)	10%Vpp	-	10%VDD		
Duty	45	55	45	55	%	
Output Level (Clipped Sine Wave)	0.8	12	0.8	_	Vp-p	
Load (CMOS)	15pF		15pF			
Load (Clipped Sine Wave)	10 KΩ // 10pF		10 KΩ // 10pF			
Control Voltage Range (VCTCXO)	0.5	2.5	0.5	2.5	V	
Pulling Range (VCTCXO)	±5.0	12	±5.0	_	ppm	
Vc Input Impedance (VCTCXO)	100	-	100	12	kΩ	
Phase Noise @ 10 MHz		dBc/Hz				
	-154					
Start time	<u>-</u>	2	_	2	mSec	
Storage Temp. Range	-55	125	-55	125	°C	

Standard frequencies are frequencies which the crystal has been designed and does not imply a stock position,

FREQ. STABILITY vs. TEMP. RANGE

Temp. (°C) ppm	±0.05	±0.1	±0.14	±0.2	±0.28	±0.5	±2
-10 ~ +70	0	0	0	0	0	0	0
-20 ~ +70	×	0	0	0	0	0	0
-40 ~ +85	×	×	×	Δ	0	0	0
-40 ~ +95	×	×	×	×	×	Δ	0
-40 ~ +105	×	×	×	×	×	×	0

^{* ○:} Available △: Conditional X: Not available

^{*}Frequency at 25°C, 1 hour after reflow